

ABSTRACT

A system and method for determining the logic state of a magnetic tunnel junction (MTJ) memory device. The method includes applying a first bias voltage to a selected line and measuring a first induced voltage across the MJT device or a memory cell. The method also includes applying a second bias voltage to the selected line, the second bias voltage being different from the first bias voltage, and measuring a second induced voltage across the MJT device. The method also includes comparing a function of the first bias voltage, the first induced voltage, the second bias voltage, and the second induced voltage to a threshold value.